

A METHOD AND STRUCTURE FOR IMPROVED ALIGNMENT TOLERANCE
IN MULTIPLE, SINGULARIZED PLUGS

Abstract of the Disclosure

5 An improved method and structure which increases the alignment tolerances in multiple, singularized plugs are provided. The invention discloses a novel method for forming individual plug contacts with increased surface area for improved registration between semiconducting layers. Also the improved plug contacts are particularly well suited to receiving contact formations which have any
10 taper to them. IGFETS and other devices formed from this design can be used in a variety of beneficial applications, e.g. logic or memory.

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